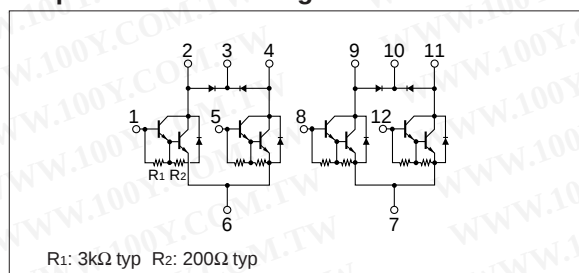


($T_a=25^{\circ}\text{C}$)

Symbol	Ratings	Unit
V _{CB0}	120	V
V _{CE0}	100	V
V _{EB0}	6	V
I _C	3	A
I _{CP}	5 (PW≤1ms, Du≤50%)	A
I _B	0.2	A
I _F	3 (PW≤0.5ms, Du≤25%)	A
I _{FSM}	5 (PW≤10ms, Single pulse)	A
V _R	120	V
P _T	4 (T _a =25°C)	W
	20 (T _c =25°C)	
T _j	150	°C
T _{stg}	-40 to +150	°C

■Equivalent circuit diagram



Electrical characteristics

($T_a=25^{\circ}\text{C}$)

Symbol	Specification			Unit	Conditions
	min	typ	max		
ICBO			10	μA	$V_{CB}=120\text{V}$
IEBO			10	mA	$V_{EB}=6\text{V}$
V_{CE0}	100			V	$I_C=25\text{mA}$
h_{FE}	2000	6000	15000		$V_{CE}=4\text{V}$, $I_C=1.5\text{A}$
$V_{CE(sat)}$		1.1	1.5	V	$I_C=1.5\text{A}$, $I_B=3\text{mA}$
$V_{BE(sat)}$		1.7	2.0	V	
t_{on}		0.5		μs	$V_{CC} \div 30\text{V}$, $I_C=1.5\text{A}$, $I_{B1}=-I_{B2}=3\text{mA}$
t_{stg}		2.2		μs	
t_f		0.9		μs	
f_r		40		MHz	$V_{CE}=12\text{V}$, $I_E=-0.5\text{A}$
C_{ob}		30		pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

●Diode for flyback voltage absorption

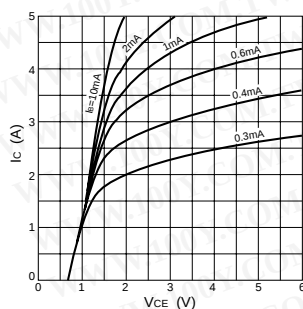
($T_a=25^{\circ}\text{C}$)

Symbol	Specification			Unit	Conditions
	min	typ	max		
V_R	120			V	$I_R=10\mu A$
V_F			1.6	V	$I_F=1A$
I_R			10	μA	$V_R=120V$
t_{rr}		100		ns	$I_F=\pm 100mA$

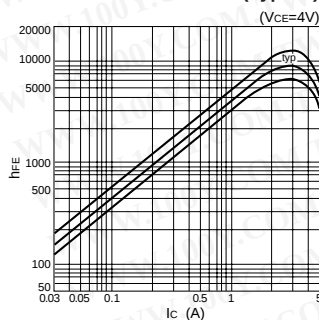
勝特力材料 886-3-5753170
勝特力電子(上海) 86-21-34970699
勝特力電子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Characteristic curves

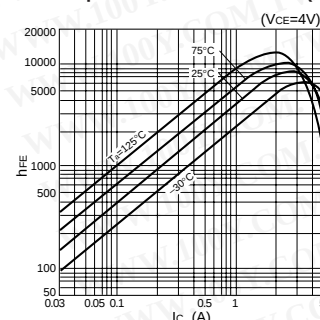
IC-V_{CE} Characteristics (Typical)



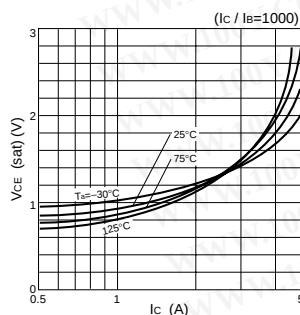
hFE-1C Characteristics (Typical)



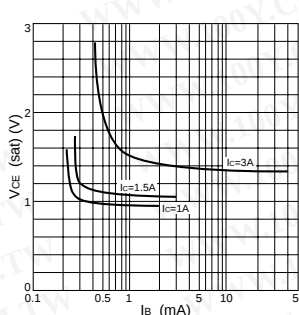
h_{FE}-I_C Temperature Characteristics (Typical)



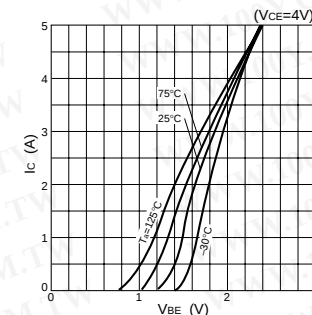
V_{CE(sat)}-I_C Temperature Characteristics (Typical)



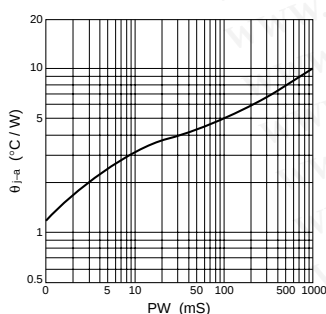
V_{CE(sat)}-I_B Characteristics (Typical)



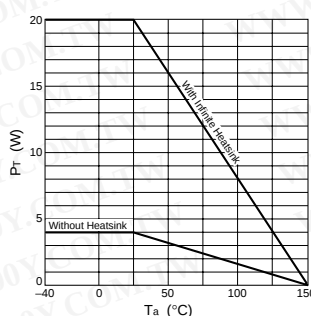
IC-V_{BE} Temperature Characteristics (Typical)



θ_{j-a} -PW Characteristics



P_T-T_a Characteristics



Safe Operating Area (SOA)

